

**IN THE CLAIMS:**

The following is a list of all claims with status indicators.

1. (previously amended) An integrated circuit structure comprising:

a chip carrier;

at least one integrated circuit chip containing structures which may be affected by external magnetic fields, said integrated circuit chip having a front surface and a back surface, said front surface being supported by said chip carrier, and wherein said structures which may be affected by external magnetic fields include a magnetic random access memory device;

a first magnetic field shielding material in contact with said back surface of said chip; and

a second magnetic field shielding material in contact with said chip carrier, such that said magnetic random access memory device is located between said first and second magnetic field shielding materials.

2. (previously amended) The structure of claim 1, wherein said first shielding material is in the form of a first layer of said magnetic field shielding material on said back surface.

3. (previously amended) The structure of claim 1, wherein said first shielding material comprises a magnetic material selected from the group consisting of ferrites, manganites, chromites and cobaltites.

4. (original) The structure of claim 3, wherein said magnetic material comprises  $MFe_2O_4$ , wherein M is at least one atom selected from the group consisting of Mn, Fe, Co, Ni, Cu, and Mg.

5. (original) The structure of claim 3, wherein said magnetic material comprises a material which includes conductive particles.

6. (original) The structure of claim 5, wherein said magnetic material comprises a material which includes nickel particles.

7. (original) The structure of claim 5, wherein said magnetic material comprises a material which includes iron particles.

8. (original) The structure of claim 5, wherein said magnetic material comprises a material which includes cobalt particles.

Claims 9-10 canceled.

11. (original) The structure of claim 1, wherein said chip carrier is a flip-chip carrier.

12. (canceled)

13. (previously amended) The structure of claim 11, wherein said second magnetic field shielding layer comprises a magnetic material selected from the group consisting of ferrites, manganites, chromites and cobaltites.

14. (original) The structure of claim 13, wherein said magnetic material comprises  $MFe_2O_4$ , wherein M is at least one atom selected from the group consisting of Mn, Fe, Co, Ni, Cu, and Mg.

15. (original) The structure of claim 13, wherein said magnetic material comprises a material which includes conductive particles.

16. (original) The structure of claim 15, wherein said magnetic material comprises a material which includes nickel particles.

17. (original) The structure of claim 15, wherein said magnetic material comprises a material which includes cobalt particles.

18. (original) The structure of claim 15, wherein said magnetic material comprises a material which includes iron particles.

19. (original) The structure of claim 11 further comprising a printed circuit board having an upper surface and a bottom surface, said upper surface supporting said flip-chip carrier.

20. (original) The structure of claim 19, wherein said printed circuit board further comprises a third magnetic field shielding layer.

21. (original) The structure of claim 20, wherein said third magnetic field shielding layer is located on said upper surface of said printed circuit board.

22. (original) The structure of claim 20, wherein said third magnetic field shielding layer is located on said bottom surface of said printed circuit board.

23. (original) The structure of claim 20, wherein said third magnetic field shielding layer is embedded within said printed circuit board.

24. (original) The structure of claim 20, wherein said third magnetic field shielding layer comprises  $MFe_2O_4$ , wherein M is at least one atom selected from the group consisting of Mn, Fe, Co, Ni, Cu, and Mg.

25. (original) The structure of claim 20, wherein said magnetic material comprises a material which includes conductive particles.

26. (original) The structure of claim 25, wherein said magnetic material comprises a material which includes nickel particles.

27. (original) The structure of claim 20, wherein said printed circuit board further comprises a fourth magnetic field shielding layer in contact with said bottom surface, said third magnetic field shielding layer being embedded within said printed circuit board.

28. (original) The structure of claim 27, wherein each of said fourth and third magnetic field shielding layers comprises a magnetic material selected from the group consisting of ferrites, manganites, chromites and cobaltites.

29. (original) The structure of claim 28, wherein said magnetic material comprises  $MFe_2O_4$ , wherein M is at least one atom selected from the group consisting of Mn, Fe, Co, Ni, Cu, and Mg.

30. (original) The structure of claim 28, wherein said magnetic material comprises a material which includes conductive particles.

31. (original) The structure of claim 30, wherein said magnetic material comprises a material which includes nickel particles.

Claims 32-63 canceled.

64. (previously amended) An integrated circuit structure comprising:

a die carrier;

a die electrically connected to said die carrier, said die being in contact with a first layer of magnetic field shielding material, said die further comprising a magnetic random access memory device; and

a printed circuit board electrically connected to said die carrier, said printed circuit board being in contact with a second layer of magnetic field shielding material, and wherein said magnetic random access memory device is located between said first and second layers of magnetic field shielding material.

65. (original) The integrated circuit structure of claim 64, wherein said die carrier comprises a third layer of magnetic field shielding material.

66. (original) The integrated circuit structure of claim 65, wherein each of said first, second and third layers of magnetic field shielding material comprises a magnetic material selected from the group consisting of ferrites, manganites, chromites and cobaltites.

67. (original) The integrated circuit structure of claim 66, wherein said magnetic material comprises  $MFe_2O_4$ , wherein M is at least one atom selected from the group consisting of Mn, Fe, Co, Ni, Cu, and Mg.

68. (original) The integrated circuit structure of claim 66, wherein said magnetic material comprises a material which includes conductive particles.

69. (original) The integrated circuit structure of claim 68, wherein said conductive particles are selected from the group consisting of nickel particles, iron particles, and cobalt particles.

70. (previously amended) A method of packaging a semiconductor device comprising:

electrically coupling a die carrier to a first surface of a die, said first surface being opposite to a second surface of said die, and wherein said die includes a magnetic random access memory device;

contacting said second surface of said die with a first layer of magnetic field shielding material which shields said die from external magnetic fields, wherein said second surface is a back surface of the die; and

contacting said die carrier with a second layer of magnetic field shielding material which shields said die from external magnetic fields, such that said memory device is located between said first and second layers of magnetic field shielding material.

71. (previously amended) The method of claim 70 further comprising the act of electrically coupling said die carrier to a printed circuit board.

72. (previously amended) The method of claim 71, wherein a third layer of magnetic field shielding material is formed on a surface of said printed circuit board.

73. (previously amended) The method of claim 72, wherein said third layer of magnetic field shielding material is formed on a top surface of said printed circuit board.

74. (previously amended) The method of claim 72, wherein said third layer of magnetic field shielding material is formed on a bottom surface of said printed circuit board.

75. (previously amended) The method of claim 72, wherein said third layer of magnetic field shielding material is embedded within said printed circuit board.

76. (previously amended) The method of claim 72, wherein said third layer of magnetic field shielding material is formed on both a bottom surface and a top surface of said printed circuit board.

Claims 77-78 canceled.

79. (original) The method of claim 70, wherein said first layer of magnetic field shielding material comprises a magnetic material selected from the group consisting of ferrites, manganites, chromites and cobaltites.

80. (original) The method of claim 79, wherein said magnetic material comprises  $MFe_2O_4$ , wherein M is at least one atom selected from the group consisting of Mn, Fe, Co, Ni, Cu, and Mg.

81. (original) The method of claim 79, wherein said magnetic material comprises a material which includes conductive particles.

82. (original) The method of claim 81, wherein said conductive particles are selected from the group consisting of nickel particles, iron particles, and cobalt particles.

83. (original) The method of claim 71, wherein said second layer of magnetic field shielding material comprises a magnetic material selected from the group consisting of ferrites, manganites, chromites and cobaltites.

84. (original) The method of claim 83, wherein said magnetic material comprises  $MFe_2O_4$ , wherein M is at least one atom selected from the group consisting of Mn, Fe, Co, Ni, Cu, and Mg.

85. (original) The method of claim 83, wherein said magnetic material comprises a material which includes conductive particles.

86. (original) The method of claim 85, wherein said magnetic material comprises a material which includes nickel particles.

Claims 87-96 canceled.